Marius Grundmann

List of Publications by Year
in descending order

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781 papers	29,683 citations	7096 78 h-index	8866 145 g-index
804 all docs	804 docs citations	804 times ranked	18425 citing authors

#	Article	IF	Citations
1	InAs/GaAs pyramidal quantum dots: Strain distribution, optical phonons, and electronic structure. Physical Review B, 1995, 52, 11969-11981.	3.2	1,144
2	Electronic and optical properties of strained quantum dots modeled by 8-band kâ‹…p theory. Physical Review B, 1999, 59, 5688-5701.	3.2	999
3	Low threshold, large To injection laser emission from (InGa)As quantum dots. Electronics Letters, 1994, 30, 1416-1417.	1.0	787
4	Ultranarrow Luminescence Lines from Single Quantum Dots. Physical Review Letters, 1995, 74, 4043-4046.	7.8	721
5	High electron mobility of epitaxial ZnO thin films on c-plane sapphire grown by multistep pulsed-laser deposition. Applied Physics Letters, 2003, 82, 3901-3903.	3.3	596
6	Raman scattering in ZnO thin films doped with Fe, Sb, Al, Ga, and Li. Applied Physics Letters, 2003, 83, 1974-1976.	3.3	595
7	Infrared dielectric functions and phonon modes of high-quality ZnO films. Journal of Applied Physics, 2003, 93, 126-133.	2.5	590
8	Zinc oxide nanorod based photonic devices: recent progress in growth, light emitting diodes and lasers. Nanotechnology, 2009, 20, 332001.	2.6	572
9	Advances in designs and mechanisms of semiconducting metal oxide nanostructures for high-precision gas sensors operated at room temperature. Materials Horizons, 2019, 6, 470-506.	12.2	493
10	Direct formation of vertically coupled quantum dots in Stranski-Krastanow growth. Physical Review B, 1996, 54, 8743-8750.	3.2	491
11	Room temperature ferromagnetism in ZnO films due to defects. Applied Physics Letters, 2008, 92, 082508.	3.3	329
12	Radiative recombination in typeâ€Ⅱ GaSb/GaAs quantum dots. Applied Physics Letters, 1995, 67, 656-658.	3.3	313
13	Theory of random population for quantum dots. Physical Review B, 1997, 55, 9740-9745.	3.2	309
14	Whispering Gallery Modes in Nanosized Dielectric Resonators with Hexagonal Cross Section. Physical Review Letters, 2004, 93, 103903.	7.8	291
15	Defect-induced magnetic order in pure ZnO films. Physical Review B, 2009, 80, .	3.2	274
16	The 2016 oxide electronic materials and oxide interfaces roadmap. Journal Physics D: Applied Physics, 2016, 49, 433001.	2.8	266
17	Transparent flexible thermoelectric material based on non-toxic earth-abundant p-type copper iodide thin film. Nature Communications, 2017, 8, 16076.	12.8	233
18	Multiphononâ€relaxation processes in selfâ€organized InAs/GaAs quantum dots. Applied Physics Letters, 1996, 68, 361-363.	3.3	231

#	Article	IF	Citations
19	Carrier dynamics in type-II GaSb/GaAs quantum dots. Physical Review B, 1998, 57, 4635-4641.	3.2	231
20	Excited states and energy relaxation in stacked InAs/GaAs quantum dots. Physical Review B, 1998, 57, 9050-9060.	3.2	228
21	Close-to-ideal device characteristics of high-power InGaAs/GaAs quantum dot lasers. Applied Physics Letters, 2001, 78, 1207-1209.	3.3	224
22	Excited states in selfâ€•organized InAs/GaAs quantum dots: Theory and experiment. Applied Physics Letters, 1996, 68, 979-981.	3.3	216
23	Ordered arrays of quantum dots: Formation, electronic spectra, relaxation phenomena, lasing. Solid-State Electronics, 1996, 40, 785-798.	1.4	206
24	Radiative states in type-II GaSb/GaAs quantum wells. Physical Review B, 1995, 52, 14058-14066.	3.2	205
25	The Physics of Semiconductors. Graduate Texts in Physics, 2010, , .	0.2	202
26	The present status of quantum dot lasers. Physica E: Low-Dimensional Systems and Nanostructures, 1999, 5, 167-184.	2.7	199
27	Structural characterization of (In,Ga)As quantum dots in a GaAs matrix. Physical Review B, 1995, 51, 14766-14769.	3.2	196
28	Whispering gallery mode lasing in zinc oxide microwires. Applied Physics Letters, 2008, 92, 241102.	3.3	192
29	MgxZn1âˆ’xO(0â©½x<0.2) nanowire arrays on sapphire grown by high-pressure pulsed-laser deposition. Applied Physics Letters, 2005, 86, 143113.	3.3	188
30	Room temperature ferromagnetism in carbon-implanted ZnO. Applied Physics Letters, 2008, 93, .	3.3	188
31	Room-temperature synthesized copper iodide thin film as degenerate p-type transparent conductor with a boosted figure of merit. Proceedings of the National Academy of Sciences of the United States of America, 2016, 113, 12929-12933.	7.1	188
32	Quantum dot lasers: breakthrough in optoelectronics. Thin Solid Films, 2000, 367, 235-249.	1.8	187
33	Quantum-dot heterostructure lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 439-451.	2.9	183
34	Cuprous iodide - a p-type transparent semiconductor: history and novel applications. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1671-1703.	1.8	178
35	Dielectric functions (1 to 5 eV) of wurtzite MgxZn1âˆ’xOâ€Š(xâ©½0.29) thin films. Applied Physics Letters, 2003, 82, 2260-2262.	3.3	165
36	InAsâ€“GaAs Quantum Pyramid Lasers: In Situ Growth, Radiative Lifetimes and Polarization Properties. Japanese Journal of Applied Physics, 1996, 35, 1311-1319.	1.5	164

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37	Raman tensor elements of Î²-Ga2O3. Scientific Reports, 2016, 6, 35964.	3.3	162
38	Scanning cathodoluminescence microscopy: A unique approach to atomic-scale characterization of heterointerfaces and imaging of semiconductor inhomogeneities. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2358.	1.6	156
39	The Physics of Semiconductors. Graduate Texts in Physics, 2016, , .	0.2	155
40	Mean barrier height of Pd Schottky contacts on ZnO thin films. Applied Physics Letters, 2006, 88, 092102.	3.3	154
41	The contribution of particle core and surface to strain, disorder and vibrations in thiolcapped CdTe nanocrystals. Journal of Chemical Physics, 1998, 108, 7807-7815.	3.0	153
42	Electron escape from InAs quantum dots. Physical Review B, 1999, 60, 14265-14268.	3.2	146
43	Optical and electrical properties of epitaxial (Mg,Cd)xZn1âˆ’xO, ZnO, and ZnO:(Ga,Al) thin films on c-plane sapphire grown by pulsed laser deposition. Solid-State Electronics, 2003, 47, 2205-2209.	1.4	140
44	Recent Progress on ZnOâ€Based Metalâ€Semiconductor Fieldâ€Effect Transistors and Their Application in Transparent Integrated Circuits. Advanced Materials, 2010, 22, 5332-5349.	21.0	140
45	Image charges in semiconductor quantum wells: Effect on exciton binding energy. Physical Review B, 1990, 42, 5906-5909.	3.2	136
46	Defects in virgin andN+-implanted ZnO single crystals studied by positron annihilation, Hall effect, and deep-level transient spectroscopy. Physical Review B, 2006, 74, .	3.2	135
47	Transparent p-CuI/n-ZnO heterojunction diodes. Applied Physics Letters, 2013, 102, .	3.3	135
48	Transparent semiconducting oxides: materials and devices. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1437-1449.	1.8	129
49	InAs/GaAs quantum dots radiative recombination from zeroâ€dimensional states. Physica Status Solidi (B): Basic Research, 1995, 188, 249-258.	1.5	127
50	A Practical, Selfâ€Catalytic, Atomic Layer Deposition of Silicon Dioxide. Angewandte Chemie - International Edition, 2008, 47, 6177-6179.	13.8	127
51	Band-structure pseudopotential calculation of zinc-blende and wurtzite AlN, GaN, and InN. Physical Review B, 2003, 67, .	3.2	124
52	High-power quantum-dot lasers at 1100 nm. Applied Physics Letters, 2000, 76, 556-558.	3.3	116
53	Nanoscroll formation from strained layer heterostructures. Applied Physics Letters, 2003, 83, 2444-2446.	3.3	113
54	Optical signatures of deep level defects in Ga2O3. Applied Physics Letters, 2018, 112, .	3.3	113

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55	Determination of the mean and the homogeneous barrier height of Cu Schottky contacts on heteroepitaxial Î²â€Ga₂O₃ thin films grown by pulsed laser deposition. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 40-47.	1.8	111
56	Binding Specificity of a Peptide on Semiconductor Surfaces. Nano Letters, 2004, 4, 2115-2120.	9.1	110
57	Gain and Threshold of Quantum Dot Lasers: Theory and Comparison to Experiments. Japanese Journal of Applied Physics, 1997, 36, 4181-4187.	1.5	109
58	Phosphorus acceptor doped ZnO nanowires prepared by pulsed-laser deposition. Nanotechnology, 2007, 18, 455707.	2.6	109
59	Self-organization processes in MBE-grown quantum dot structures. Thin Solid Films, 1995, 267, 32-36.	1.8	108
60	Lateral homogeneity of Schottky contacts on n-type ZnO. Applied Physics Letters, 2004, 84, 79-81.	3.3	108
61	Low-order optical whispering-gallery modes in hexagonal nanocavities. Physical Review A, 2005, 72, .	2.5	105
62	Epitaxial stabilization of pseudomorphic Î±-Ga₂O₃on sapphire (0001). Applied Physics Express, 2015, 8, 011101.	2.4	104
63	Tin-assisted heteroepitaxial PLD-growth of Îº-Ga2O3 thin films with high crystalline quality. APL Materials, 2019, 7, .	5.1	98
64	Lowâ€temperature metalorganic chemical vapor deposition of InP on Si(001). Applied Physics Letters, 1991, 58, 284-286.	3.3	97
65	Growth, Spectroscopy, and Laser Application of Self-Ordered III-V Quantum Dots. MRS Bulletin, 1998, 23, 31-34.	3.5	96
66	Multiferroic BaTiO₃â€“BiFeO₃composite thin films and multilayers: strain engineering and magnetoelectric coupling. Journal Physics D: Applied Physics, 2014, 47, 135303.	2.8	96
67	Selfâ€organization processes of InGaAs/GaAs quantum dots grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 68, 3284-3286.	3.3	92
68	Control of the conductivity of Siâ€doped Î²â€<scp>G</scp>a₂<scp>O</scp>₃ thin films via growth temperature and pressure. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 34-39.	1.8	92
69	Room-temperature Domain-epitaxy of Copper Iodide Thin Films for Transparent CuI/ZnO Heterojunctions with High Rectification Ratios Larger than 109. Scientific Reports, 2016, 6, 21937.	3.3	91
70	Cuprous iodide - a p-type transparent semiconductor: history and novel applications (Phys. Status) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	1.8	90
71	Anionic and cationic substitution in ZnO. Progress in Solid State Chemistry, 2009, 37, 153-172.	7.2	85
72	Room temperature ferromagnetism in Mn-doped ZnO films mediated by acceptor defects. Applied Physics Letters, 2007, 91, .	3.3	84

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73	Metal-insulator transition in Co-dopedZnO: Magnetotransport properties. Physical Review B, 2006, 73, .	3.2	83
74	Oxide bipolar electronics: materials, devices and circuits. Journal Physics D: Applied Physics, 2016, 49, 213001.	2.8	83
75	Band dispersion relations of zinc-blende and wurtzite InN. Physical Review B, 2004, 69, .	3.2	82
76	Infrared optical properties of MgxZn1â^'xO thin films (0â©½xâ©½1): Long-wavelength optical phonons and dielectric constants. Journal of Applied Physics, 2006, 99, 113504.	2.5	82
77	Dielectric tensor of monoclinic Ga₂O₃ single crystals in the spectral range 0.5â€“8.5 eV. APL Materials, 2015, 3, 106106.	5.1	81
78	Anisotropy effects on excitonic properties in realistic quantum wells. Physical Review B, 1988, 38, 13486-13489.	3.2	79
79	Nature of optical transitions in self-organized InAs/GaAs quantum dots. Physical Review B, 1996, 53, R10509-R10511.	3.2	79
80	Lateral and vertical ordering in multilayered self-organized InGaAs quantum dots studied by high resolution x-ray diffraction. Applied Physics Letters, 1997, 70, 955-957.	3.3	78
81	Spatially Inhomogeneous Impurity Distribution in ZnO Micropillars. Nano Letters, 2004, 4, 797-800.	9.1	78
82	Whispering gallery modes in zinc oxide microâ€•and nanowires. Physica Status Solidi (B): Basic Research, 2010, 247, 1282-1293.	1.5	77
83	Lattice parameters and Raman-active phonon modes of Î²-(AlxGa1â^'x)2O3. Journal of Applied Physics, 2015, 117, .	2.5	75
84	Ultrafast carrier capture and long recombination lifetimes in GaAs quantum wires grown on nonplanar substrates. Applied Physics Letters, 1992, 61, 67-69.	3.3	73
85	Properties of reactively sputtered Ag, Au, Pd, and Pt Schottky contacts on n-type ZnO. Journal of Vacuum Science & Technology B, 2009, 27, 1769.	1.3	73
86	Raman active phonon modes of cubic In₂O₃. Physica Status Solidi - Rapid Research Letters, 2014, 8, 554-559.	2.4	73
87	Occurrence of Rotation Domains in Heteroepitaxy. Physical Review Letters, 2010, 105, 146102.	7.8	72
88	InAsâ€GaAs quantum dots: From growth to lasers. Physica Status Solidi (B): Basic Research, 1996, 194, 159-173.	1.5	71
89	Electrical and magnetic properties of RE-doped ZnO thin films (RE = Gd, Nd). Superlattices and Microstructures, 2007, 42, 231-235.	3.1	71
90	Influence of In/Ga intermixing on the optical properties of InGaAs/GaAs quantum dots. Journal of Crystal Growth, 1998, 195, 540-545.	1.5	70

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91	Semiâ€transparent NiO/ZnO UV photovoltaic cells. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 30-37.	1.8	69
92	Anisotropic and inhomogeneous strain relaxation in pseudomorphic In0.23Ga0.77As/GaAs quantum wells. Applied Physics Letters, 1989, 55, 1765-1767.	3.3	68
93	Interfacial properties of very thin GaInAs/InP quantum well structures grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 1992, 71, 3300-3306.	2.5	68
94	Symmetry breaking in pseudomorphic V-groove quantum wires. Physical Review B, 1994, 50, 14187-14192.	3.2	68
95	Genetic discontinuity, breedingâ€system change and population history of Arabis alpina in the Italian Peninsula and adjacent Alps. Molecular Ecology, 2008, 17, 2245-2257.	3.9	68
96	Ordering phenomena in InAs strained layer morphological transformation on GaAs (100) surface. Applied Physics Letters, 1995, 67, 97-99.	3.3	67
97	Deep acceptor states in ZnO single crystals. Applied Physics Letters, 2006, 89, 092122.	3.3	67
98	Enhanced radiation hardness of quantum dot lasers to high energy proton irradiation. Electronics Letters, 2001, 37, 174.	1.0	66
99	UV optical properties of ferromagnetic Mn-doped ZnO thin films grown by PLD. Thin Solid Films, 2005, 486, 117-121.	1.8	66
100	ZnO metal-semiconductor field-effect transistors with Ag-Schottky gates. Applied Physics Letters, 2008, 92, 192108.	3.3	66
101	Infrared dielectric functions and phonon modes of wurtzite MgxZn1âˆ’xOâ€‚(xâ©½0.2). Applied Physics Letters, 2002, 81, 2376-2378.	3.3	65
102	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>s</mml:mi><mml:mtext>â€“</mml:mtext><mml:mi>d</mml:mi></mml:mrow></mml:math>exch interaction induced magnetoresistance in magnetic ZnO. Physical Review B, 2007, 76, .	3.2	65
103	Defect-induced ferromagnetism in undoped and Mn-doped zirconia thin films. Physical Review B, 2010, 82, .	3.2	65
104	Zero-dimensional excitons in (Zn,Cd)Se quantum structures. Physical Review B, 1996, 54, R11074-R11077.	3.2	64
105	Formation of epitaxial domains: Unified theory and survey of experimental results. Physica Status Solidi (B): Basic Research, 2011, 248, 805-824.	1.5	64
106	Many-body effects on the optical spectra of InAs/GaAs quantum dots. Physical Review B, 2000, 62, 16881-16885.	3.2	63
107	Influence of Pâ€Glycoprotein on the Transplacental Passage of Cyclosporine. Journal of Pharmaceutical Sciences, 2001, 90, 1583-1592.	3.3	63
108	Maximum modal gain of a self-assembled InAs/GaAs quantum-dot laser. Journal of Applied Physics, 2001, 90, 1666-1668.	2.5	62

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109	Correlation of pre-breakdown sites and bulk defects in multicrystalline silicon solar cells. Physica Status Solidi - Rapid Research Letters, 2009, 3, 70-72.	2.4	62
110	Structural characterization of a-plane Zn1âˆ’xCdxO (0â©½xâ©½0.085) thin films grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2006, 99, 023514.	2.5	61
111	Spin Manipulation in Co-Doped ZnO. Physical Review Letters, 2008, 101, 076601.	7.8	61
112	Correlation of magnetoelectric coupling in multiferroic BaTiO3-BiFeO3 superlattices with oxygen vacancies and antiphase octahedral rotations. Applied Physics Letters, 2015, 106, .	3.3	61
113	Raman Tensor Formalism for Optically Anisotropic Crystals. Physical Review Letters, 2016, 116, 127401.	7.8	61
114	Electron paramagnetic resonance ofZn1âˆ’xMnxOthin films and single crystals. Physical Review B, 2005, 72, .	3.2	60
115	Self organization phenomena of quantum dots grown by metalorganic chemical vapour deposition. Journal of Crystal Growth, 1997, 170, 568-573.	1.5	59
116	Lattice parameters and Raman-active phonon modes of (InxGa1â€“x)2O3 for xâ€‰<â€‰0.4. Journal of Applied Physics, 2014, 116, .	2.5	59
117	Schottky contacts to In2O3. APL Materials, 2014, 2, 046104.	5.1	59
118	Heteroepitaxial growth of Î±-, Î²-, Î³- and Îº-Ga2O3 phases by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2019, 510, 76-84.	1.5	59
119	Interface Recombination Current in Type II Heterostructure Bipolar Diodes. ACS Applied Materials & Interfaces, 2014, 6, 14785-14789.	8.0	57
120	Pseudopotential band structures of rocksalt MgO, ZnO, and Mg1âˆ’xZnxO. Applied Physics Letters, 2006, 88, 134104.	3.3	56
121	Structural and optical properties of (In,Ga)₂O₃ thin films and characteristics of Schottky contacts thereon. Semiconductor Science and Technology, 2015, 30, 024005.	2.0	56
122	Midinfrared emission from near-infrared quantum-dot lasers. Applied Physics Letters, 2000, 77, 4-6.	3.3	55
123	Refractive indices and band-gap properties of rocksalt MgxZn1âˆ’xO (0.68â©½xâ©½1). Journal of Applied Physics, 2006, 99, 123701.	2.5	55
124	Quantum wire heterostructure for optoelectronic applications. Superlattices and Microstructures, 1992, 12, 491-499.	3.1	54
125	Ballistic propagation of excitonâ€“polariton condensates in a ZnO-based microcavity. New Journal of Physics, 2012, 14, 013037.	2.9	54
126	Continuous composition spread using pulsed-laser deposition with a single segmented target. CrystEngComm, 2013, 15, 10020.	2.6	54

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127	Dipole analysis of the dielectric function of color dispersive materials: Application to monoclinic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Ga</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2016, 94, .	3.2	54
128	InGaAs quantum wires grown by low pressure metalorganic chemical vapor deposition on InP Vâ€grooves. Applied Physics Letters, 1996, 68, 3596-3598.	3.3	53
129	Defects in hydrothermally grown bulk ZnO. Applied Physics Letters, 2007, 91, .	3.3	53
130	Temperature-dependent dielectric and electro-optic properties of a ZnO-BaTiO3-ZnO heterostructure grown by pulsed-laser deposition. Applied Physics Letters, 2005, 86, 091904.	3.3	52
131	Low-temperature processed Schottky-gated field-effect transistors based on amorphous gallium-indium-zinc-oxide thin films. Applied Physics Letters, 2010, 97, .	3.3	52
132	Electronic structure and energy relaxation in strained InAs/GaAs quantum pyramids. Superlattices and Microstructures, 1996, 19, 81-95.	3.1	51
133	Resistive hysteresis and interface charge coupling in BaTiO3-ZnO heterostructures. Applied Physics Letters, 2009, 94, 142904.	3.3	51
134	Formation of InAs quantum dots on a silicon (100) surface. Semiconductor Science and Technology, 1998, 13, 1262-1265.	2.0	50
135	Indium Gallium Oxide Alloys: Electronic Structure, Optical Gap, Surface Space Charge, and Chemical Trends within Common-Cation Semiconductors. ACS Applied Materials & Interfaces, 2021, 13, 2807-2819.	8.0	50
136	Luminescence and surface properties of MgxZn1â^'xO thin films grown by pulsed laser deposition. Journal of Applied Physics, 2007, 101, 083521.	2.5	49
137	Donor-like defects in ZnO substrate materials and ZnO thin films. Applied Physics A: Materials Science and Processing, 2007, 88, 135-139.	2.3	49
138	Progress in Quantum Dot Lasers: 1100 nm, 1300 nm, and High Power Applications. Japanese Journal of Applied Physics, 2000, 39, 2341-2343.	1.5	48
139	Cathodoluminescence of selected single ZnO nanowires on sapphire. Annalen Der Physik, 2004, 13, 39-42.	2.4	48
140	Mott variable-range hopping and weak antilocalization effect in heteroepitaxial Na<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>IrO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>thin films. Physical Review B, 2013, 88, .	3.2	48
141	Dielectric function in the spectral range (0.5â€“8.5)eV of an (Al_x) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 1 Physics, 2015, 117, 165307.	2.5	48
142	pâ€type conducting ZnO:P microwires prepared by direct carbothermal growth. Physica Status Solidi - Rapid Research Letters, 2008, 2, 37-39.	2.4	47
143	Microscopic Mechanism of Specific Peptide Adhesion to Semiconductor Substrates. Angewandte Chemie - International Edition, 2010, 49, 9530-9533.	13.8	47
144	Defect segregation and optical emission in ZnO nano- and microwires. Nanoscale, 2016, 8, 7631-7637.	5.6	47

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145	Strain distribution in bent ZnO microwires. Applied Physics Letters, 2011, 98, 031105.	3.3	46
146	Effect of rare-earth ion doping on the multiferroic properties of BiFeO₃thin films grown epitaxially on SrTiO₃(1â€‰0â€‰0). Journal Physics D: Applied Physics, 2013, 46, 175006.	2.8	46
147	Ordered growth of tilted ZnO nanowires: morphological, structural and optical characterization. Nanotechnology, 2007, 18, 195303.	2.6	45
148	Highly rectifying p-ZnCo₂O₄/n-ZnO heterojunction diodes. Applied Physics Letters, 2014, 104, 022104.	3.3	45
149	All Amorphous Oxide Bipolar Heterojunction Diodes from Abundant Metals. Advanced Electronic Materials, 2015, 1, 1400023.	5.1	45
150	Homogeneous core/shell ZnO/ZnMgO quantum well heterostructures on vertical ZnO nanowires. Nanotechnology, 2009, 20, 305701.	2.6	44
151	Comparison of Schottky contacts on Î²-gallium oxide thin films and bulk crystals. Applied Physics Express, 2015, 8, 121102.	2.4	44
152	UVâ€“VUV spectroscopic ellipsometry of ternary MgxZn1â^'xO (0â‰¤xâ‰¤0.53) thin films. Thin Solid Films, 2004, 455-456, 500-504.	1.8	43
153	Magnetoresistance and anomalous Hall effect in magnetic ZnO films. Journal of Applied Physics, 2007, 101, 063918.	2.5	43
154	Dependence of structural and optical properties of In0.23Ga0.77As/GaAs quantum wells on misfit dislocations: Different critical thickness for dislocation generation and degradation of optical properties. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 751.	1.6	42
155	Ferromagnetic transition metal implanted ZnO: A diluted magnetic semiconductor?. Vacuum, 2009, 83, S13-S19.	3.5	42
156	Observation of strong excitonâ€“photon coupling at temperatures up to 410â€‰K. New Journal of Physics, 2009, 11, 073044.	2.9	42
157	Homoepitaxy of ZnO by pulsed-laser deposition. Physica Status Solidi - Rapid Research Letters, 2007, 1, 129-131.	2.4	41
158	Selfâ€•organized growth of ZnOâ€•based nanoâ€•and microstructures. Physica Status Solidi (B): Basic Research, 2010, 247, 1265-1281.	1.5	41
159	High mobility, highly transparent, smooth, p-type CuI thin films grown by pulsed laser deposition. APL Materials, 2020, 8, .	5.1	41
160	Enhanced Radiation Hardness of InAs/GaAs Quantum Dot Structures. Physica Status Solidi (B): Basic Research, 2001, 224, 93-96.	1.5	40
161	Excitonâ€“polariton formation at room temperature in a planar ZnO resonator structure. Applied Physics B: Lasers and Optics, 2008, 93, 331-337.	2.2	40
162	Identification of pre-breakdown mechanism of silicon solar cells at low reverse voltages. Applied Physics Letters, 2010, 97, .	3.3	39

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163	ELECTRONIC AND OPTICAL PROPERTIES OF QUASI-ONE-DIMENSIONAL CARRIERS IN QUANTUM WIRES. Journal of Nonlinear Optical Physics and Materials, 1995, 04, 99-140.	1.8	38
164	Room-temperature ferromagnetic Mn-alloyed ZnO films obtained by pulsed laser deposition. Journal of Magnetism and Magnetic Materials, 2006, 307, 212-221.	2.3	38
165	Paramagnetism in Co-doped ZnO films. Journal Physics D: Applied Physics, 2009, 42, 085001.	2.8	38
166	Interface polarization coupling in piezoelectric-semiconductor ferroelectric heterostructures. Physical Review B, 2010, 81, .	3.2	38
167	Visible-blind and solar-blind ultraviolet photodiodes based on (InxGa1â^'x)2O3. Applied Physics Letters, 2016, 108, .	3.3	38
168	Epitaxial stabilization of single phase Î²-(InxGa1â^'x)2O3 thin films up to x = 0.28 on c-sapphire and Î²-Ga2O3(001) templates by tin-assisted VCCS-PLD. APL Materials, 2019, 7, .	5.1	38
169	SnO/Î²-Ga2O3 vertical pn heterojunction diodes. Applied Physics Letters, 2020, 117, .	3.3	38
170	Recombination kinetics and intersubband relaxation in semiconductor quantum wires. Semiconductor Science and Technology, 1994, 9, 1939-1945.	2.0	37
171	Spatial fluctuations of optical emission from single ZnO/MgZnO nanowire quantum wells. Nanotechnology, 2008, 19, 115202.	2.6	37
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